MITSUBISHI ELECTRIC

< IGBT MODULES >

CM400DY-34A

HIGH POWER SWITCHING USE
INSULATED TYPE

Collector current I_C .... **400** A

Collector-emitter voltage V_{CES} .... **1700** V
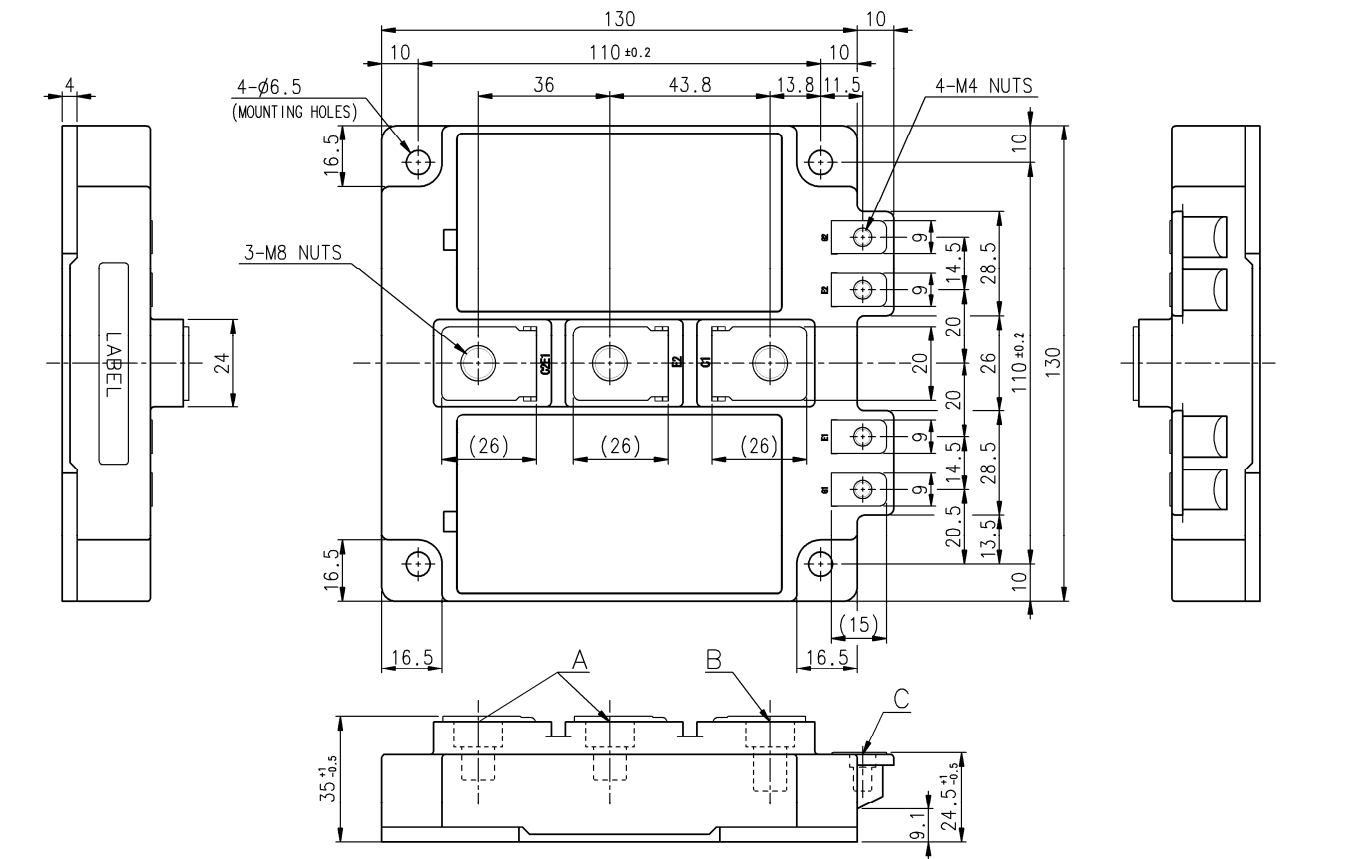
Maximum junction temperature T_{jmax} .... **150** °C

- Flat base Type
- Copper base plate (non-plating)
- RoHS Directive compliant
- UL Recognized under UL1557, File E323585

Dual (Half-Bridge)

APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm

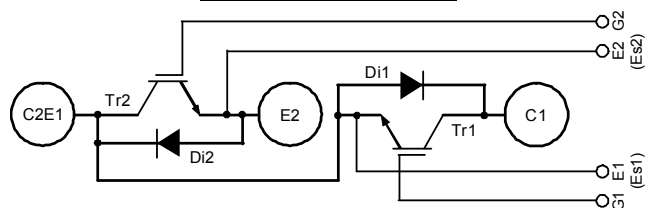### TERMINAL SCREW HOLE DEPTH

	L	M
A	16	7
B	19	7
C	10	3.5

Tolerance otherwise specified

Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2

INTERNAL CONNECTION

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ABSOLUTE MAXIMUM RATINGS (T_j=25 °C, unless otherwise specified)

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1700	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	±20	V
I_C	Collector current	DC, T_C=107 °C (Note.2, 4)	400	A
I_{CRM}		Pulse, Repetitive (Note.3)	800	
P_{tot}	Total power dissipation	T_C=25 °C (Note.2, 4)	3780	W
I_E (Note.1)	Emitter current	T_C=25 °C (Note.2, 4)	400	A
I_{ERM} (Note.1)		Pulse, Repetitive (Note.3)	800	
T_j	Junction temperature	-	-40 ~ +150	°C
T_{stg}	Storage temperature	-	-40 ~ +125	
V_{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	3500	V

ELECTRICAL CHARACTERISTICS (T_j=25 °C, unless otherwise specified)

Symbol	Item	Conditions		Min.	Typ.	Max.	Unit
I_{CES}	Collector-emitter cut-off current	V_{CE}=V_{CES}, G-E short-circuited		-	-	1.0	mA
I_{GES}	Gate-emitter leakage current	V_{GE}=V_{GES}, C-E short-circuited		-	-	2.0	µA
$V_{GE(th)}$	Gate-emitter threshold voltage	I_C=40 mA, V_{CE}=10 V		5.5	7.0	8.5	V
V_{CEsat}	Collector-emitter saturation voltage	I_C=400 A (Note.5),	T_j=25 °C	-	2.2	2.8	V
		V_{GE}=15 V	T_j=125 °C	-	2.45	-	
C_{ies}	Input capacitance	V_{CE}=10 V, G-E short-circuited		-	-	98.8	nF
C_{oes}	Output capacitance			-	-	11.2	
C_{res}	Reverse transfer capacitance			-	-	2.1	
Q_G	Gate charge	V_{CC}=1000 V, I_C=400 A, V_{GE}=15 V		-	2670	-	nC
$t_{d(on)}$	Turn-on delay time	V_{CC}=1000 V, I_C=400 A, V_{GE}=±15 V,		-	-	950	ns
t_r	Rise time			-	-	300	
$t_{d(off)}$	Turn-off delay time	R_G=1.2 Ω, Inductive load		-	-	1000	
t_f	Fall time			-	-	350	
V_{EC} (Note.1)	Emitter-collector voltage	I_E=400 A (Note.5), G-E short-circuited		-	2.3	3.0	V
t_{rr} (Note.1)	Reverse recovery time	V_{CC}=1000 V, I_E=400 A, V_{GE}=±15 V,		-	-	450	ns
Q_{rr} (Note.1)	Reverse recovery charge	R_G=1.2 Ω, Inductive load		-	40	-	µC
E_{on}	Turn-on switching energy per pulse	V_{CC}=1000 V, I_C=I_E=400 A,		-	197.3	-	mJ
E_{off}	Turn-off switching energy per pulse	V_{GE}=±15 V, R_G=1.2 Ω, T_j=125 °C,		-	117.9	-	
E_{rr} (Note.1)	Reverse recovery energy per pulse	Inductive load		-	98.5	-	mJ
r_g	Internal gate resistance	Per switch, T_c=25 °C		-	3.7	-	Ω

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Min.	Typ.	Max.	Unit
$R_{th(j-c)Q}$	Thermal resistance (Note.2)	Junction to case, per IGBT	-	-	33	K/kW
$R_{th(j-c)D}$		Junction to case, per FWDi	-	-	55	K/kW
$R_{th(c-s)}$	Contact thermal resistance (Note.2)	Case to heat sink, per 1/2 module, Thermal grease applied (Note.6)	-	19	-	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions		Min.	Typ.	Max.	Unit
M_t	Mounting torque	Main terminals	M 8 screw	8.8	9.7	10.8	N·m
		Auxiliary (G, E) terminals	M 4 screw	1.3	1.5	1.7	
M_s		Mounting to heat sink	M 6 screw	3.5	4.0	4.5	N·m
m	Weight	-		-	1200	-	g
e_c	Flatness of base plate	On the centerline X, Y (Note.7)		-100	-	+100	µm

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Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (FWDi).
   2. Case temperature (T_C) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
      The heat sink thermal resistance should measure just under the chips.
   3. Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed T_{jmax} rating.
   4. Junction temperature (T_j) should not increase beyond T_{jmax} rating.
   5. Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
   6. Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K).
   7. Base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.
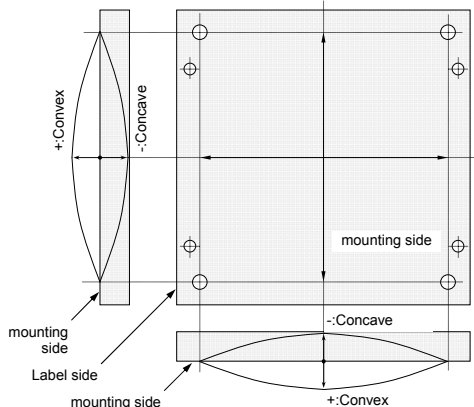
RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across C1-E2	-	1000	1100	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2	13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	1.2	-	12	Ω

CHIP LOCATION (Top view)

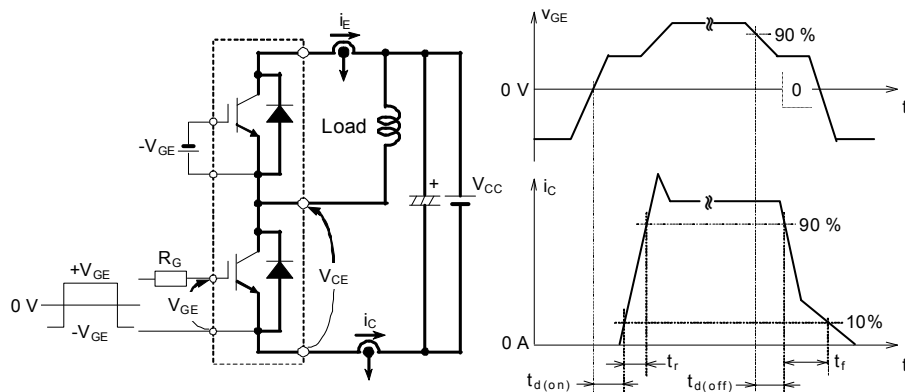Dimension in mm, tolerance: ±1 mm
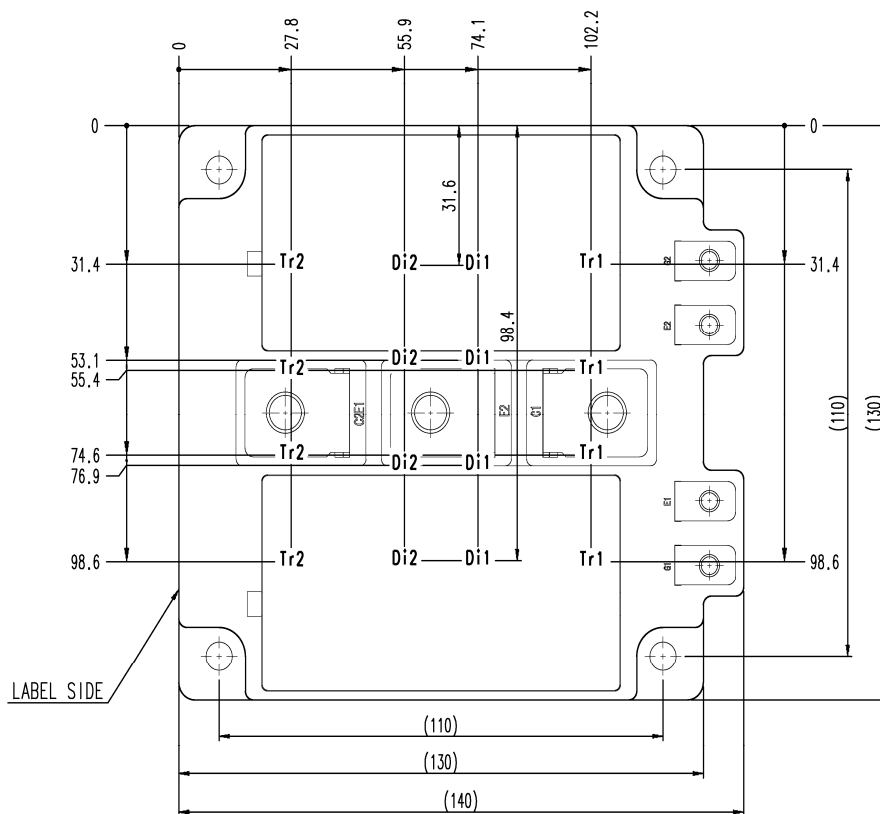
Tr1/Tr2: IGBT, Di1/Di2: FWDi

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TEST CIRCUIT AND WAVEFORMS

Tr1   **Tr2**   **Di1**   **Di2**
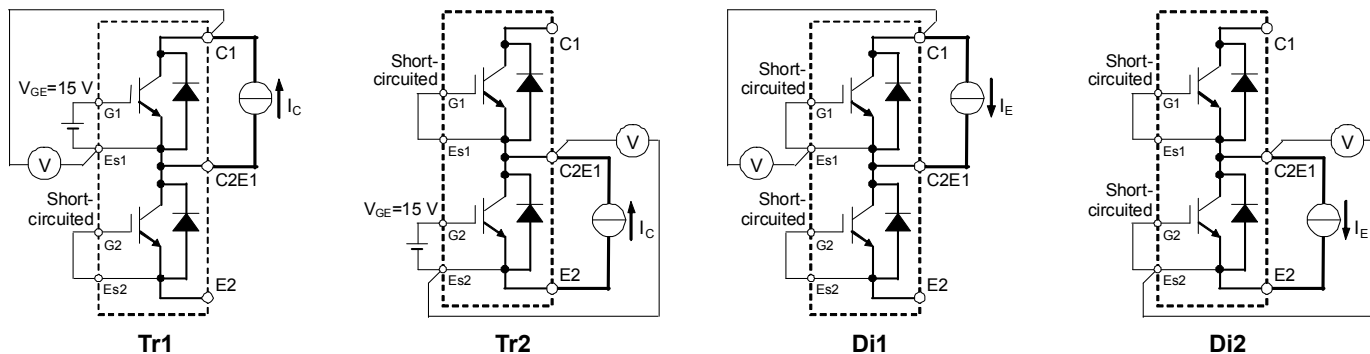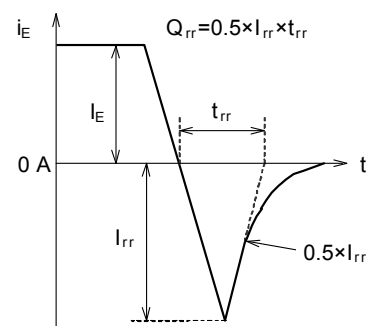
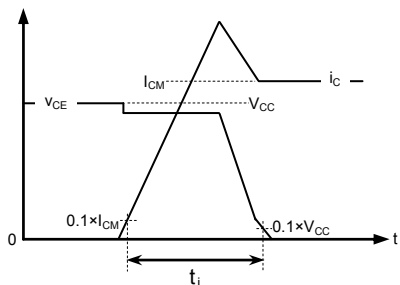V_{CEsat} **test circuit** V_{EC} **test circuit**
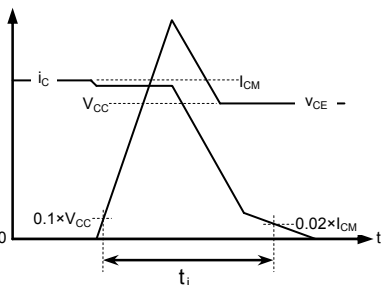
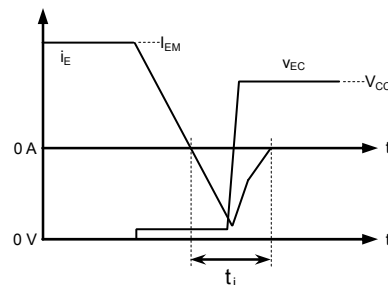**Switching characteristics test circuit and waveforms** t_{rr}, Q_{rr} **test waveform**

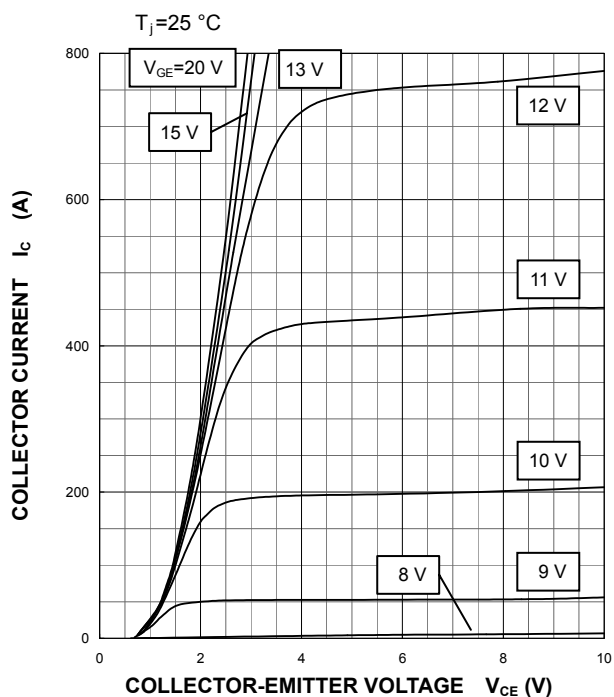**IGBT Turn-on switching energy**   **IGBT Turn-off switching energy**   **FWDi Reverse recovery energy**

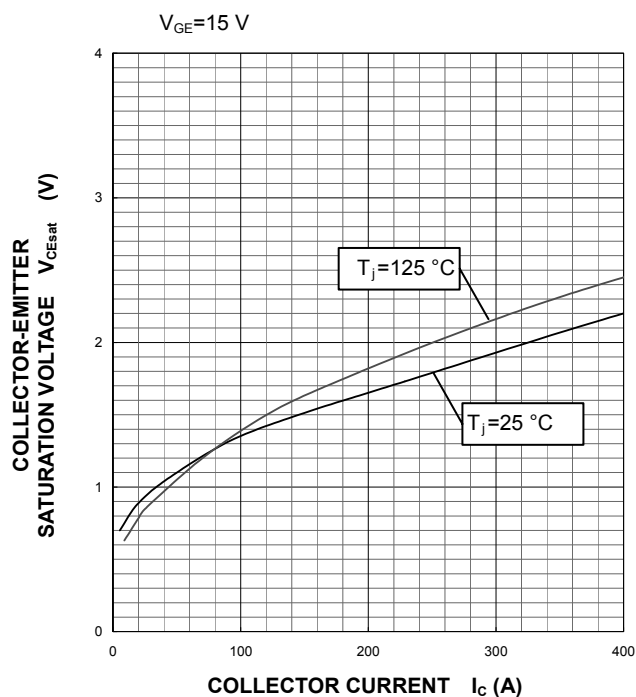**Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)**

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PERFORMANCE CURVES

OUTPUT CHARACTERISTICS
(TYPICAL)

T_j=25 °C

COLLECTOR CURRENT I_C (A)

V_{GE}=20 V, 13 V, 15 V, 12 V, 11 V, 10 V, 8 V, 9 V

COLLECTOR-EMITTER VOLTAGE V_{CE} (V)

COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)

V_{GE}=15 V

COLLECTOR-EMITTER SATURATION VOLTAGE V_{CEsat} (V)

T_j=125 °C

T_j=25 °C

COLLECTOR CURRENT I_C (A)

COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)

T_j=25 °C

COLLECTOR-EMITTER SATURATION VOLTAGE V_{CEsat} (V)

I_C=800 A

I_C=400 A

I_C=160 A

GATE-EMITTER VOLTAGE V_{GE} (V)
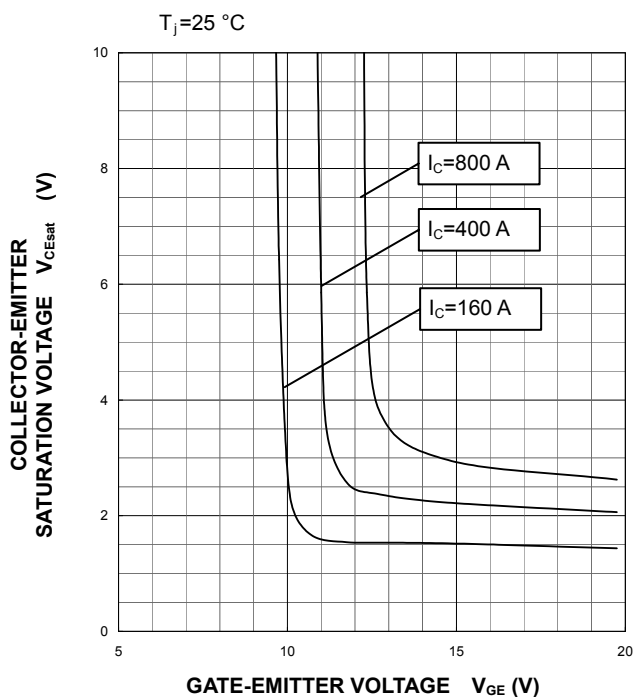
FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)

G-E short-circuited

EMITTER CURRENT I_E (A)

T_j=125 °C

T_j=25 °C

EMITTER-COLLECTOR VOLTAGE V_{EC} (V)
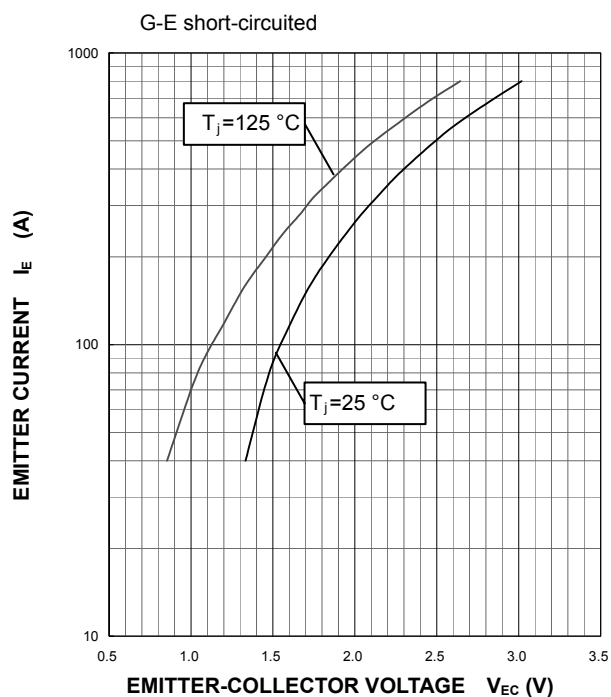
< IGBT MODULES >

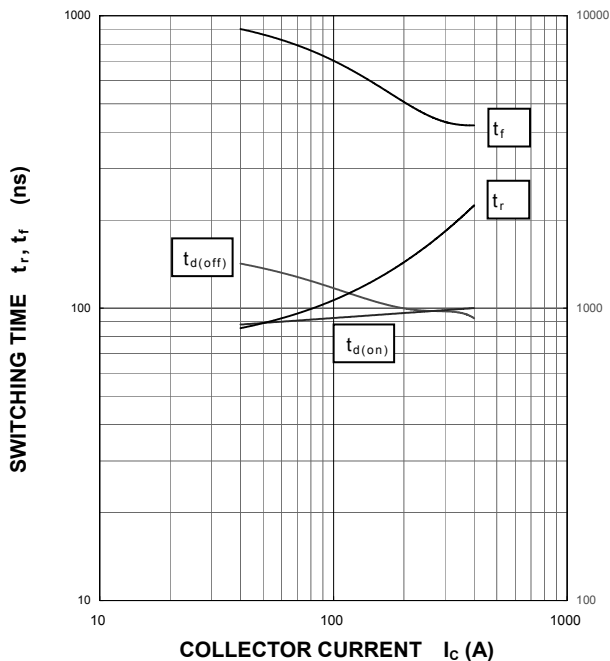# CM400DY-34A

HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)
V_{CC}=1000 V, V_{GE}=±15 V, R_G=1.2 Ω,
T_j=125 °C, INDUCTIVE LOAD

HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)
V_{CC}=1000 V, I_C=400 A, V_{GE}=±15 V,
T_j=125 °C, INDUCTIVE LOAD
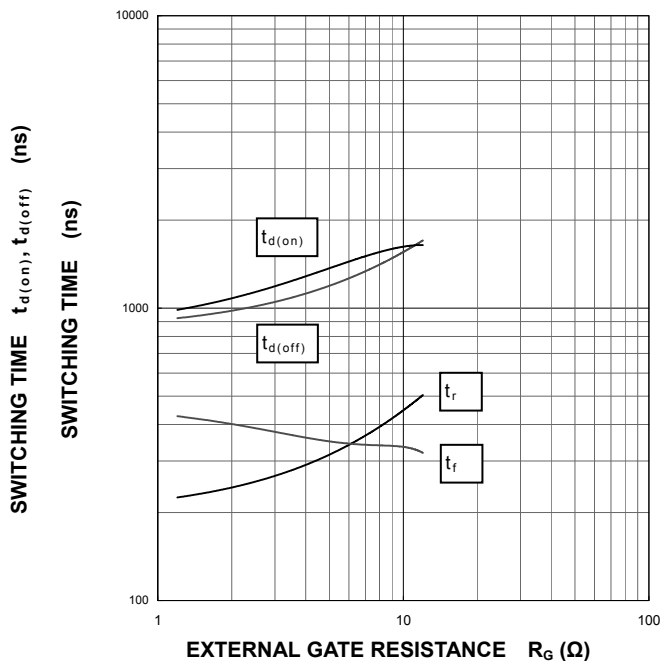
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)
V_{CC}=1000 V, V_{GE}=±15 V, R_G=1.2 Ω, T_j=125 °C
INDUCTIVE LOAD, PER PULSE
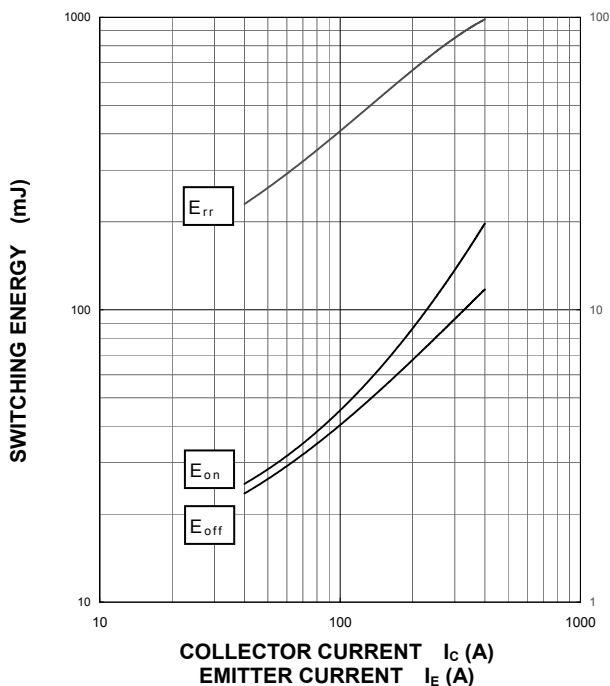
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)
V_{CC}=1000 V, I_C/I_E=400 A, V_{GE}=±15 V, T_j=125 °C
INDUCTIVE LOAD, PER PULSE

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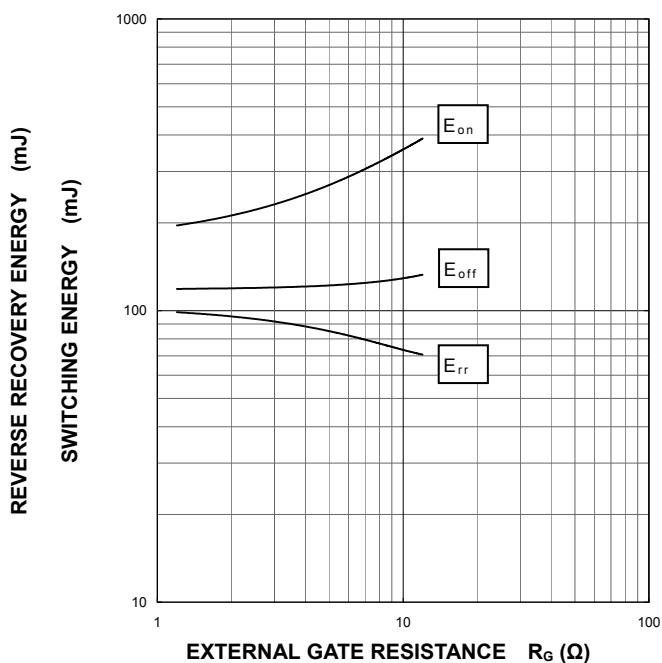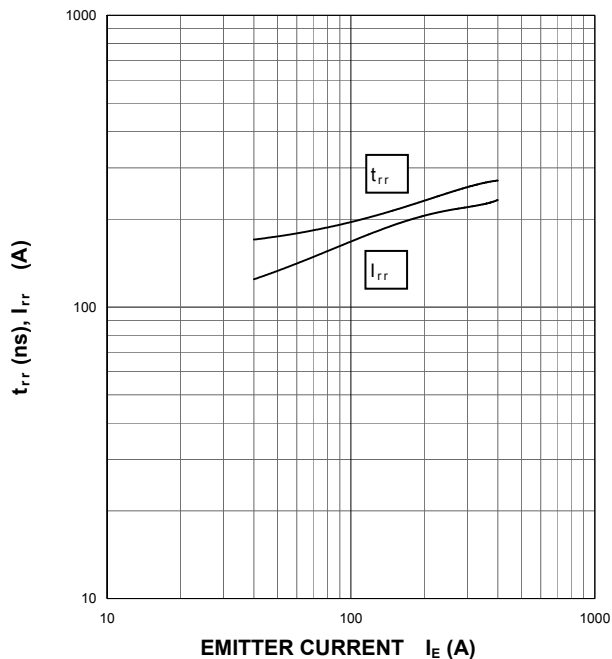
PERFORMANCE CURVES

CAPACITANCE CHARACTERISTICS
(TYPICAL)

G-E short-circuited, T_j=25 °C
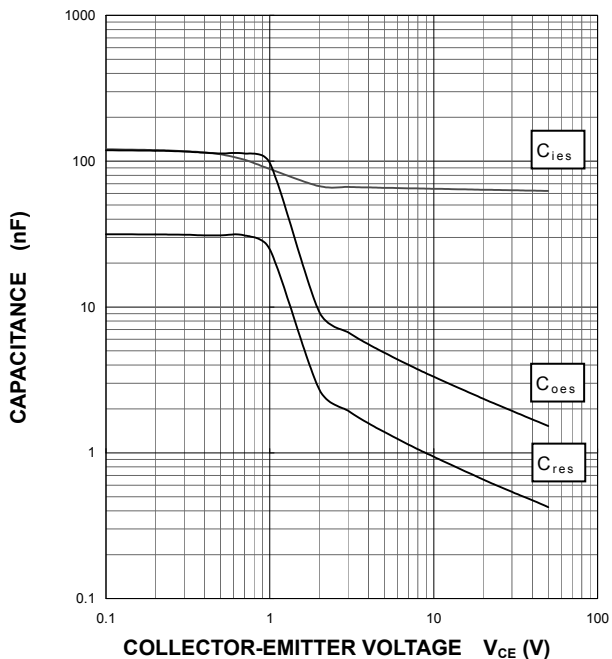
FREE WHEELING DIODE
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)

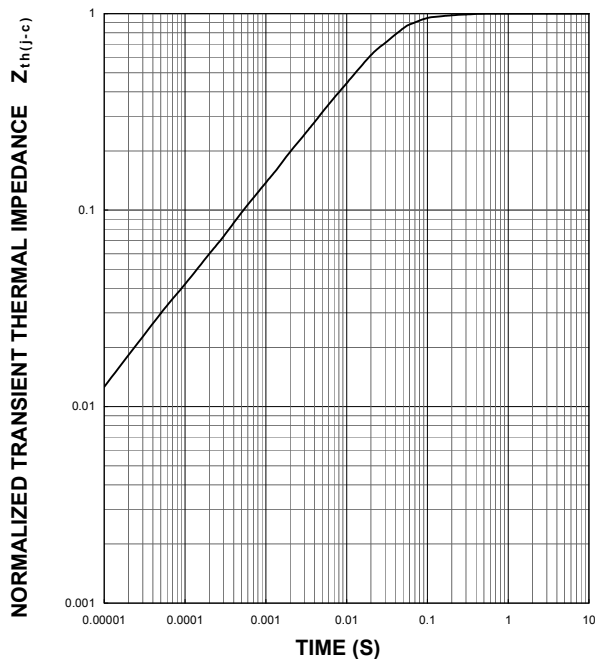V_{CC}=1000 V, V_{GE}=±15 V, R_G=1.2 Ω,
T_j=25 °C, INDUCTIVE LOAD

GATE CHARGE CHARACTERISTICS
(TYPICAL)

I_C=400 A, T_j=25 °C
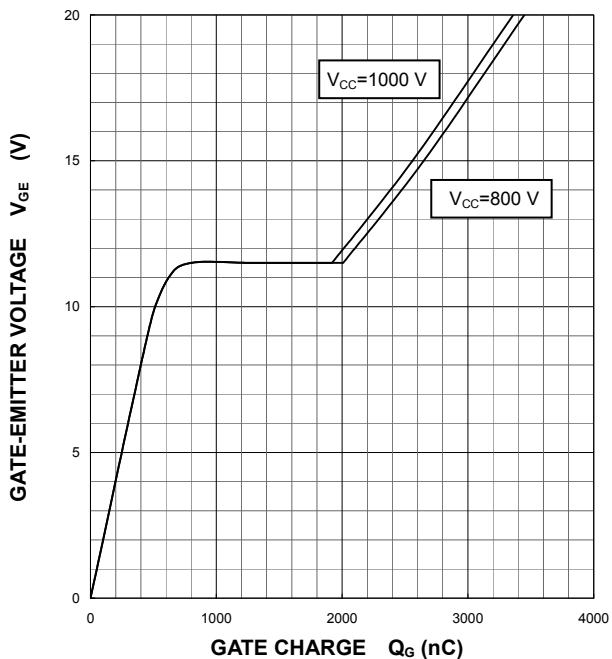
TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)

Single pulse, T_C=25°C
$R_{th(j-c)Q}$=33 K/kW, $R_{th(j-c)D}$=55 K/kW

Keep safety first in your circuit designs!

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